

Supporting Information

Atomic Layer Deposition of PbS Thin Films at Low Temperatures

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Table S1. Energetics of reactions considered in the discussion of the mechanism of elemental lead formation with Pb(dbda) at higher temperatures. The energies are calculated at the temperature of 298.15 K.

Reaction	ΔH (kJ/mol)	ΔS (kJ/K mol)	ΔG (kJ/mol)
<i>PbS deposition reactions</i>			
$\text{Pb}(\text{btsa})_2 + \text{H}_2\text{S} \rightarrow \text{PbS (s)} + 2 \text{H}(\text{btsa})$	-230	0.074	-250
$\text{Pb}(\text{dbda}) + \text{H}_2\text{S} \rightarrow \text{PbS (s)} + \text{H}_2(\text{dbda})$	-300	-0.10	-270
<i>Pb(dbda) thermolysis</i>			
$\text{Pb}(\text{dbda}) \rightarrow \text{Pb} + 2 \text{N-tert-butylacetaldehyde}$	82	0.088	56
$\text{H}_2(\text{dbda}) \rightarrow 2 \text{N-tert-butylacetaldehyde} + \text{H}_2$	150	0.36	43
$\text{Pb}(\text{dbda}) + \text{H}_2(\text{dbda}) \rightarrow \text{Pb} + \text{H}_2 + 4 \text{N-tert-butylacetaldehyde}$	240	0.45	110
<i>Reduction by H₂S</i>			
$\text{Pb}(\text{btsa})_2 + \text{H}_2\text{S} \rightarrow \text{Pb (s)} + 2 \text{H}(\text{btsa}) + \frac{1}{8} \text{S}_8$	8.9	-0.073	31
$\text{Pb}(\text{dbda}) + \text{H}_2\text{S} \rightarrow \text{Pb (s)} + \text{H}_2(\text{dbda}) + \frac{1}{8} \text{S}_8$	-41	-0.30	48
<i>Etching by Pb precursor</i>			
$\text{Pb}(\text{btsa})_2 + \text{PbS (s)} \rightarrow 2 \text{Pb (s)} + \text{S}(\text{btsa})_2$	390	-0.32	490
$\text{Pb}(\text{dbda}) + \text{PbS (s)} \rightarrow 2 \text{Pb (s)} + \text{S}(\text{dbda})$	370	-0.32	470
<i>Etching by free ligand</i>			
$\text{PbS (s)} + 2 \text{H}(\text{btsa}) \rightarrow \text{Pb (s)} + \text{H}_2 + \text{S}(\text{btsa})_2$	410	-0.27	490
$\text{PbS (s)} + \text{H}_2(\text{dbda}) \rightarrow \text{Pb (s)} + \text{H}_2 + \text{S}(\text{dbda})$	440	-0.054	460
$\text{PbS (s)} + \text{H}_2(\text{dbda}) \rightarrow \text{Pb (s)} + \text{H}_2\text{S} + 2 \text{N-tert-butylacetaldehyde}$	360	0.24	290

Table continues on the next page →

Reaction	ΔH (kJ/mol)	ΔS (kJ/K mol)	ΔG (kJ/mol)
<i>Reduction by H₂</i>			
$\text{Pb}(\text{btsa})_2 + \text{H}_2 \rightarrow \text{Pb (s)} + 2 \text{H}(\text{btsa})$	-22	-0.046	-8.3
$\text{Pb}(\text{dbda}) + \text{H}_2 \rightarrow \text{Pb (s)} + \text{H}_2(\text{dbda})$	-71	-0.27	9.3
<i>Imine thiolysis and oligomerization</i>			
$\text{H}_2\text{S} + N\text{-tert-butylacetaldimine} \rightarrow \text{thioacetaldehyde} + t\text{-butylamine}$	27	0.011	24
$\text{H}_2\text{S} + N\text{-tert-butylacetaldimine} \rightarrow \frac{1}{3} \text{ cis-thioacetaldehyde trimer} + 2 t\text{-butylamine}$	-68	-0.12	-32
$\text{H}_2\text{S} + N\text{-tert-butylacetaldimine} \rightarrow \frac{1}{3} \text{ trans-thioacetaldehyde trimer} + 2 t\text{-butylamine}$	-66	-0.12	-30
$\text{Pb}(\text{dbda}) + 2 \text{H}_2\text{S} \rightarrow \frac{2}{3} \text{ cis-thioacetaldehyde trimer} + 2 t\text{-butylamine} + \text{Pb}$	-55	-0.15	-10
$\text{Pb}(\text{dbda}) + 2 \text{H}_2\text{S} \rightarrow \frac{2}{3} \text{ trans-thioacetaldehyde trimer} + 2 t\text{-butylamine} + \text{Pb}$	-50	-0.16	-2.3
<i>Miscellaneous</i>			
$\text{H}_2\text{S} \rightarrow \text{H}_2 + \frac{1}{8} \text{S}_8$	31	-0.027	39
$\text{PbS} \rightarrow \text{Pb} + \frac{1}{8} \text{S}_8$	240	-0.15	290
$\text{PbS (g)} \rightarrow \text{PbS (s)}$	-230	-0.16	-180
$\text{Pb (g)} \rightarrow \text{Pb (s)}$	-200	-0.11	-170

Table S2. Element concentrations measured with TOF-ERDA in PbS films deposited with Pb(btsa)₂ and Pb(dbda). The films were deposited with 1.0 s precursor pulses and purge durations. The number of deposition cycles was chosen according to Figure 1c so that the target thickness was approximately 100 nm.

	Pb(btsa)₂ – H₂S process				Pb(dbda) – H₂S process						
Dep. Temp.	65 °C	75 °C	95 °C	115 °C	45 °C	60 °C	75 °C	95 °C	115 °C	135 °C	155 °C
Pb [at. %]	50.5 ± 0.3	50.3 ± 0.3	50.3 ± 0.3	46.5 ± 0.4	45.5 ± 0.3	46.4 ± 0.3	48.0 ± 0.3	48.0 ± 0.3	59.7 ± 0.5	75.3 ± 0.5	79.8 ± 0.5
S [at. %]	47.0 ± 0.4	47.4 ± 0.5	47.1 ± 0.5	48.7 ± 0.6	51.6 ± 0.5	51.6 ± 0.5	50.5 ± 0.4	47 ± 0.5	33.5 ± 0.6	19.7 ± 0.4	16 ± 0.3
O [at. %]	1.49 ± 0.08	1.32 ± 0.08	1.32 ± 0.09	2.78 ± 0.15	1.04 ± 0.07	0.95 ± 0.06	0.8 ± 0.06	3.6 ± 0.2	4.9 ± 0.2	3.9 ± 0.2	3.5 ± 0.2
C [at. %]	0.21 ± 0.03	0.22 ± 0.04	0.27 ± 0.04	0.53 ± 0.07	0.46 ± 0.05	0.26 ± 0.04	0.26 ± 0.03	0.54 ± 0.07	0.56 ± 0.08	0.18 ± 0.04	0.23 ± 0.05
H [at. %]	0.77 ± 0.19	0.73 ± 0.20	1.00 ± 0.24	1.47 ± 0.35	1.39 ± 0.11	0.79 ± 0.12	0.48 ± 0.05	0.88 ± 0.15	1.3 ± 0.2	0.89 ± 0.12	0.51 ± 0.08
S/Pb ratio	0.93 ± 0.01	0.94 ± 0.01	0.94 ± 0.01	1.05 ± 0.02	1.13 ± 0.01	1.11 ± 0.01	1.05 ± 0.01	0.98 ± 0.01	0.56 ± 0.02	0.26 ± 0.02	0.20 ± 0.02

Table S3. Band gaps of PbS thin films reported in literature. Feature size refers either to crystallite size or to grain size depending on the method used for its determination.

Band gap (eV)	Band gap Method	Range examined (eV)	Film thicknesses (nm)	Feature size (nm)	Feature size Method	Reference
1.4 – 1.7	Tauc	0.8 – 4.5	200	-	-	Lee et al. ¹
0.9 – 1.6	Tauc	0.6 – 2.0	200	16 – 52	Scherrer	Yeon et al. ²
1.4 – 1.6	Tauc	-	-	-	-	Kaci et al. ³
0.4 – 1.5	Tauc	0.4 – 3.0	120 – 400	70 – 90	Scherrer	Sadovnikov et al. ⁴
				40 – 70	SEM	
1.7	Tauc	1.1 – 3.5	100	-	-	Kotadiya et al. ⁵
2.5 – 2.7	Tauc	1.1 – 3.1	93 - 110	60 – 217	SEM	Göde et al. ⁶
2.7	Tauc	1.0 – 3.0	750	50	SEM	Filho et al. ⁷
1.5	Tauc	1.0 – 2.0	170	100	SEM	Mohanty et al. ⁸
0.8 – 1.3	Tauc	0.6 – 1.5	250 – 400	30 – 40	Scherrer	Hone et al. ⁹
1.8	Tauc	1.4 – 2.0	-	20 – 60	SEM	Cheraghizade et al. ¹⁰
1.0 – 1.2	Tauc	0.4 – 1.4	550	7 – 30	Williamson-Hall	Veena et al. ¹¹
				400 – 600	SEM	
1.7 – 2.3	Tauc	1.0 – 3.0	600 – 1000	17 – 44	Scherrer	Abbas et al. ¹²
1.2 – 1.8	Tauc	0.4 – 2.8	150	20 – 30	Scherrer	Motlagh et al. ¹³
1.2 – 1.5	Tauc	1.0 – 2.0	-	10 – 30	Scherrer	Thangavel et al. ¹⁴
1.0 – 1.4	Tauc	1.0 – 3.5	110 – 220	-	-	Gonzalez et al. ¹⁵
0.4 – 2.8	STM	n/a	2 – 16	30 – 150	SEM	Dasgupta et al. ¹⁶

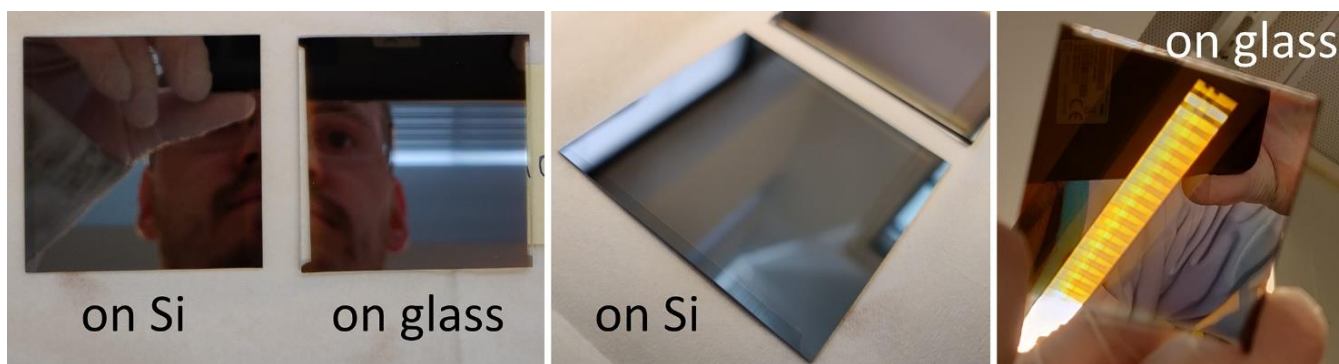


Figure S1. Photographs of PbS films deposited with $\text{Pb}(\text{btsa})_2$ and H_2S at 65 °C. Precursor pulse and purge durations were 1.0 s and the number of applied deposition cycles was 1000. PbS films deposited with $\text{Pb}(\text{dbda})$ and H_2S have similar appearance. Substrate size is 5 x 5 cm.

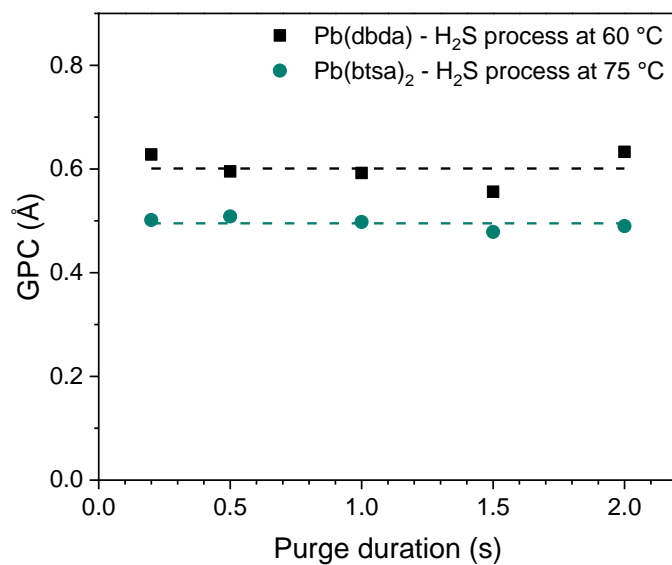


Figure S2. GPC as function of the purge duration between precursor pulses. In these experiments precursor pulse durations were fixed at 1.0 s and the number of cycles at 1000. Purge duration after both precursor pulses was varied. For example 0.5 s purge duration corresponds to a process cycle consisting of 1.0 s lead precursor pulse, 0.5 s purge, 1.0 s H_2S precursor pulse and 0.5 s purge.

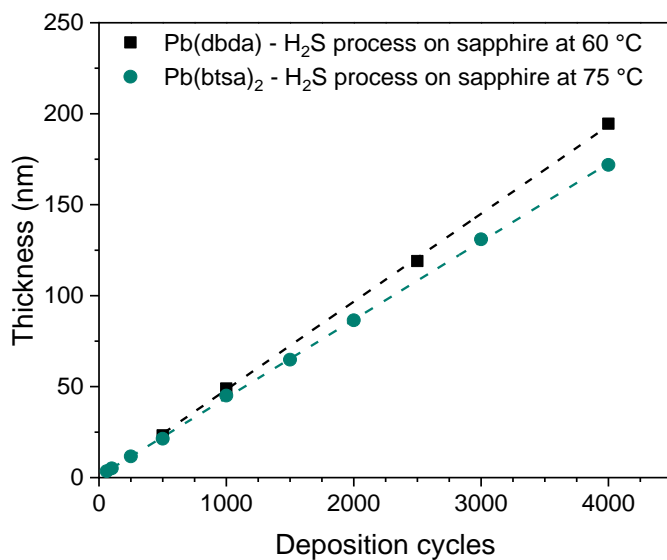


Figure S3. PbS film thickness on sapphire as a function of applied deposition cycles. Films deposited with 1.0 s precursor pulses and purge durations.

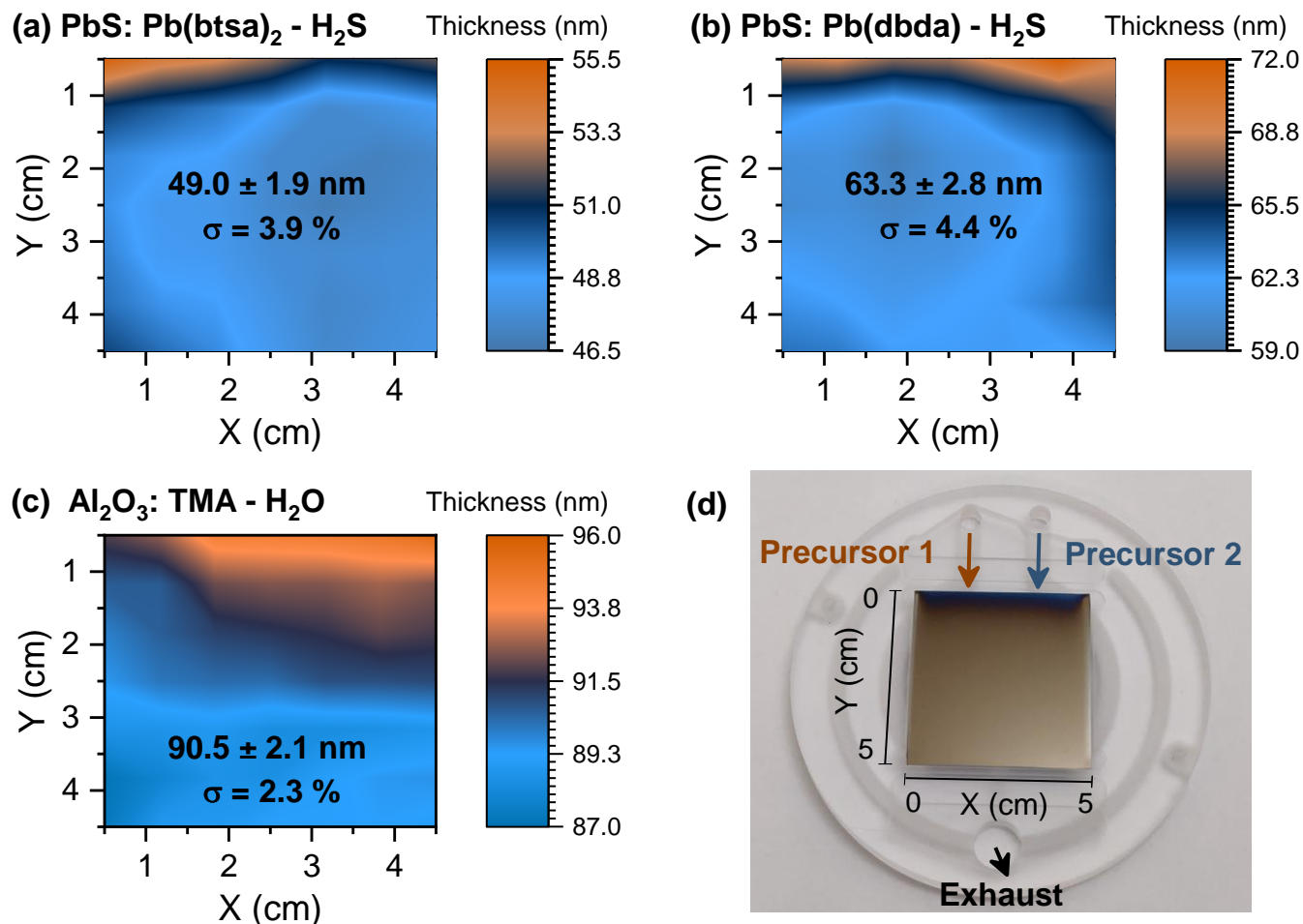


Figure S4. XRR thickness maps with 0.5 cm edge exclusion of films deposited on 5 x 5 cm² Si substrates. a) and b) are measured from PbS films deposited with 1000 cycles, 1.0 s precursor pulses and 2.0 s purge durations with Pb(btsa)₂ at 75 °C and Pb(dbda) at 60 °C respectively. c) is from a reference Al₂O₃ film deposited with trimethylaluminum (TMA) and water at 200 °C with 1000 cycles, 1.0 s precursor pulse and purge durations. In d) half of the substrate holder of the F120 ALD reactor with precursor inlets and exhaust marked with arrows is shown. If the leading edge (top 1.5 cm of the film) is excluded from the analysis, the thickness nonuniformities become 1.8 %, 2.0 % and 1.1 % for PbS made with Pb(btsa)₂, PbS made with Pb(dbda) and Al₂O₃ respectively.

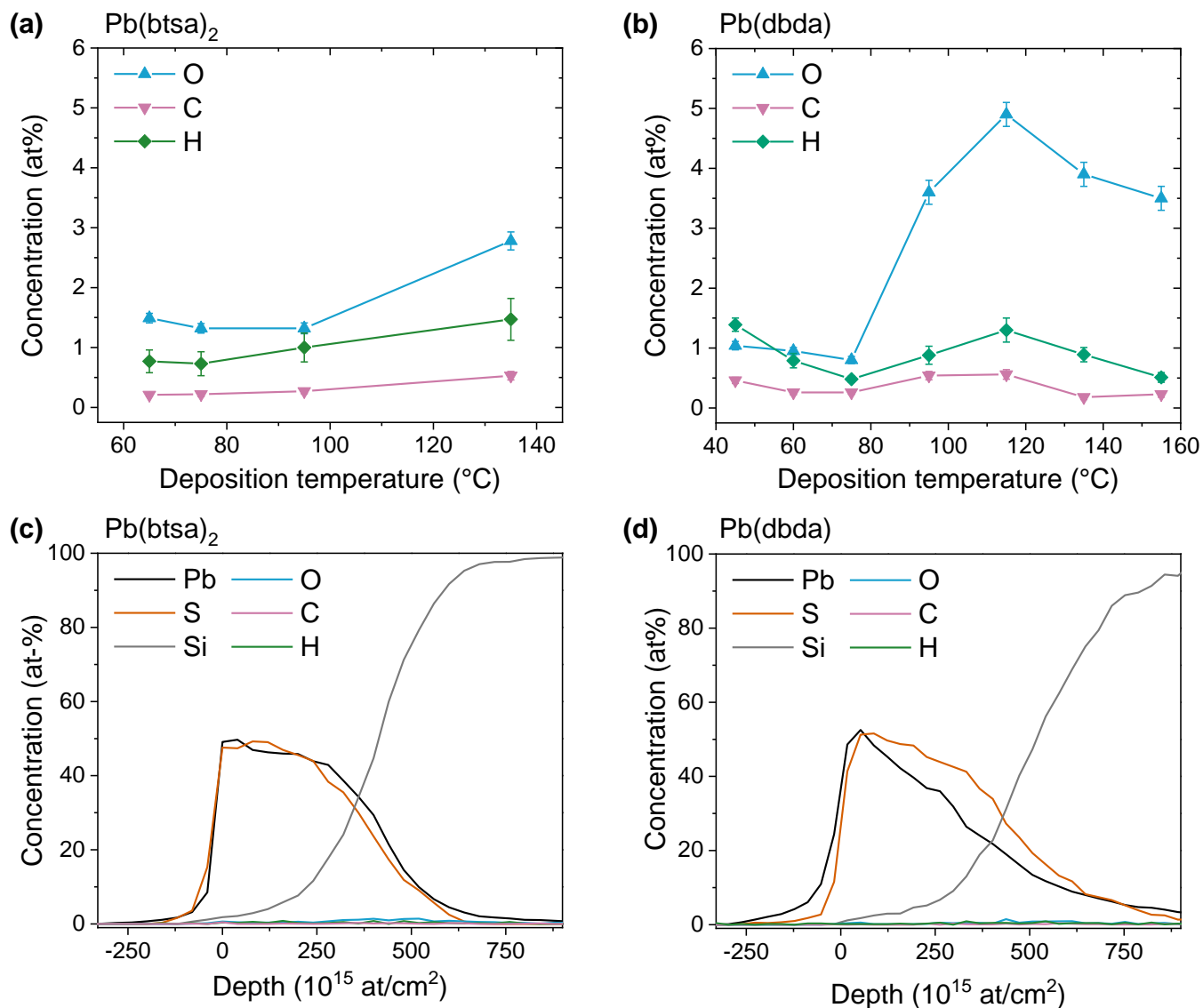


Figure S5. Impurity element concentrations measured with TOF-ERDA are shown in (a) and (b) for films made with Pb(btsa)₂ and Pb(dbda) respectively. (c) and (d) show typical TOF-ERDA depth profiles. In (c) the film was deposited with Pb(btsa)₂ at 75 °C and in (d) with Pb(dbda) at 60 °C. The films were deposited with 1.0 s precursor pulses and purge durations. The number of deposition cycles was chosen according to Figure 1c so that the target thickness was approximately 100 nm.

Pb(dbda) at 135 °C

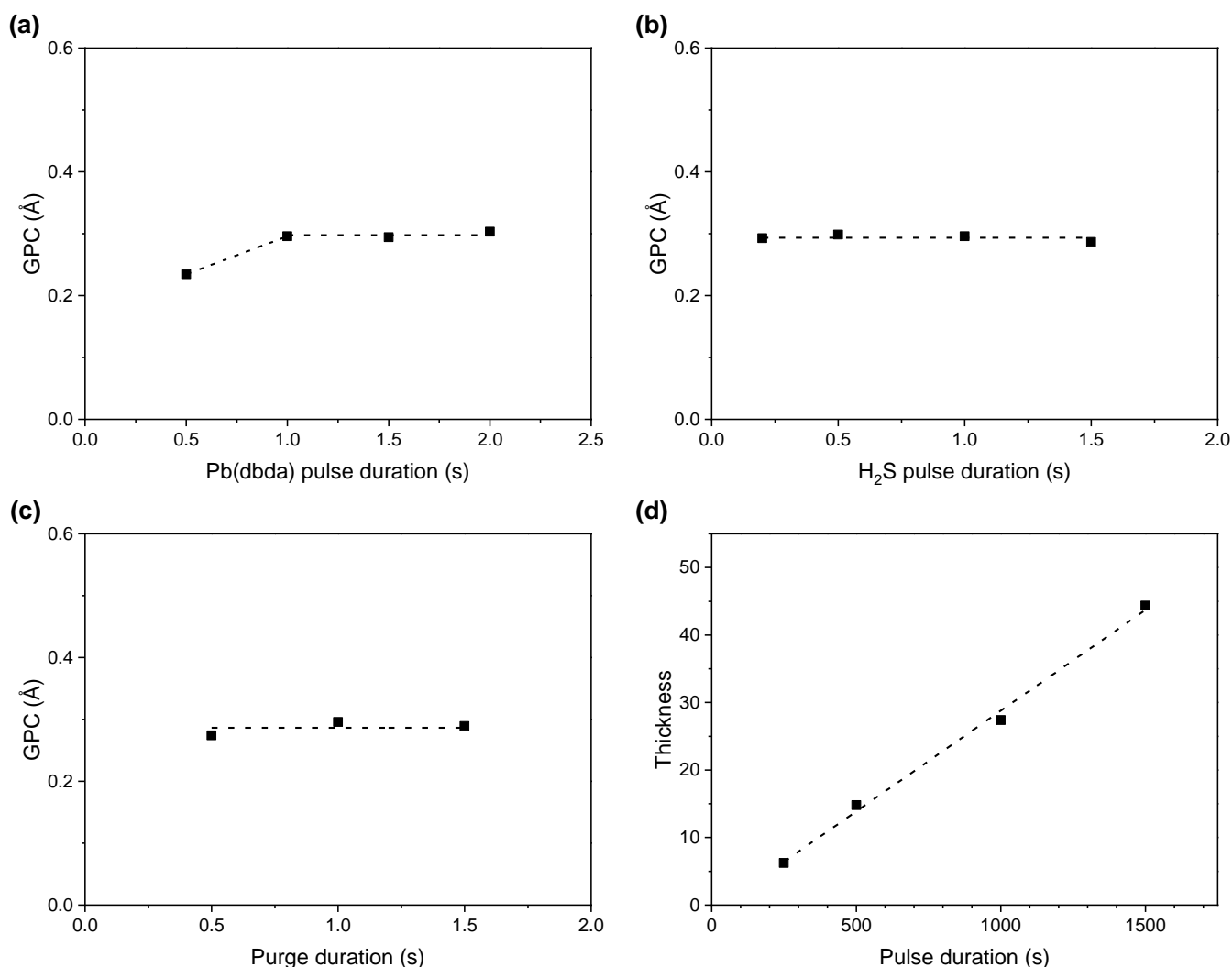


Figure S6. GPC of the PbS_x film deposited on silicon at 135 °C as a function of (a) Pb(dbda) precursor pulse duration, (b) H₂S pulse duration and (c) purge durations. (d) shows PbS_x film thickness on silicon as a function of applied deposition cycles. Unless otherwise evident, data is from films deposited with 1500 cycles, 1.0 s precursor pulses and purge durations. In (c) purge duration after both precursor pulses were varied. For example, 0.5 s purge duration corresponds to a process cycle consisting of 1.0 s lead precursor pulse, 0.5 s purge, 1.0 s H₂S precursor pulse and 0.5 s purge. In all depositions a thin underlayer (ca. 1.6 nm) and overlayer (ca. 3 nm) of Al₂O₃ was deposited prior to and after the PbS deposition. The Al₂O₃ was deposited with 1.0 s precursor pulse and 4.0 s purge durations. 25 and 50 cycles were used for the underlayer and overlayer respectively.

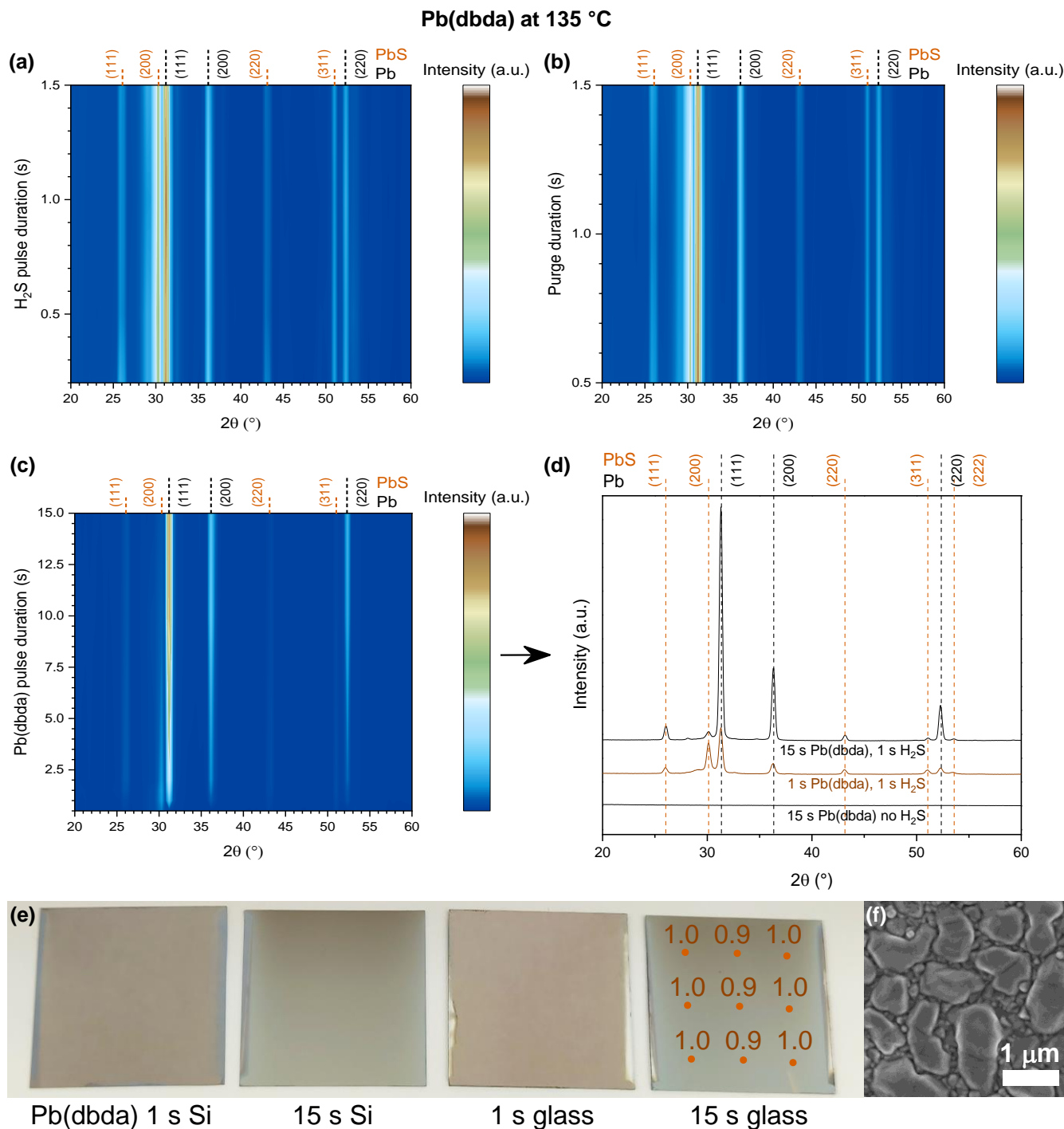


Figure S7. Contour profile maps of grazing incidence XRD (GIXRD) data for PbS_x films deposited on silicon at 135 °C as a function of (a) H_2S pulse duration, (b) purge durations and (c) $\text{Pb}(\text{dbda})$ precursor pulse duration. (d) shows GIXRD of films deposited with 15 s and 1 s $\text{Pb}(\text{dbda})$ pulse durations as well as a reference where only $\text{Pb}(\text{dbda})$ was pulsed for 15 s separated by 1.0 s purges. (e) Photographs of PbS_x films deposited on Si and soda lime glass with 1.0 s and 15 s $\text{Pb}(\text{dbda})$ pulse durations. Vermillion dots and numbers are resistivities in $\text{m}\Omega \text{ cm}$ measured at that site. (f) FESEM image of a PbS_x film deposited with 15 s long $\text{Pb}(\text{dbda})$ pulse durations. Unless otherwise evident, data is from films deposited with 1500 cycles, 1.0 s precursor pulses and purge durations. In (b) purge durations after both precursor pulses were varied. For example, 0.5 s purge duration corresponds to a process cycle consisting of 1.0 s lead precursor pulse, 0.5 s purge, 1.0 s H_2S precursor pulse and 0.5 s purge. In all depositions a thin underlayer (ca. 1.6 nm) and overlayer (ca. 3 nm) of Al_2O_3 was deposited prior to and after the PbS deposition. The Al_2O_3 was deposited with 1.0 s precursor pulse and 4.0 s purge durations. 25 and 50 cycles were used for the underlayer and overlayer respectively.

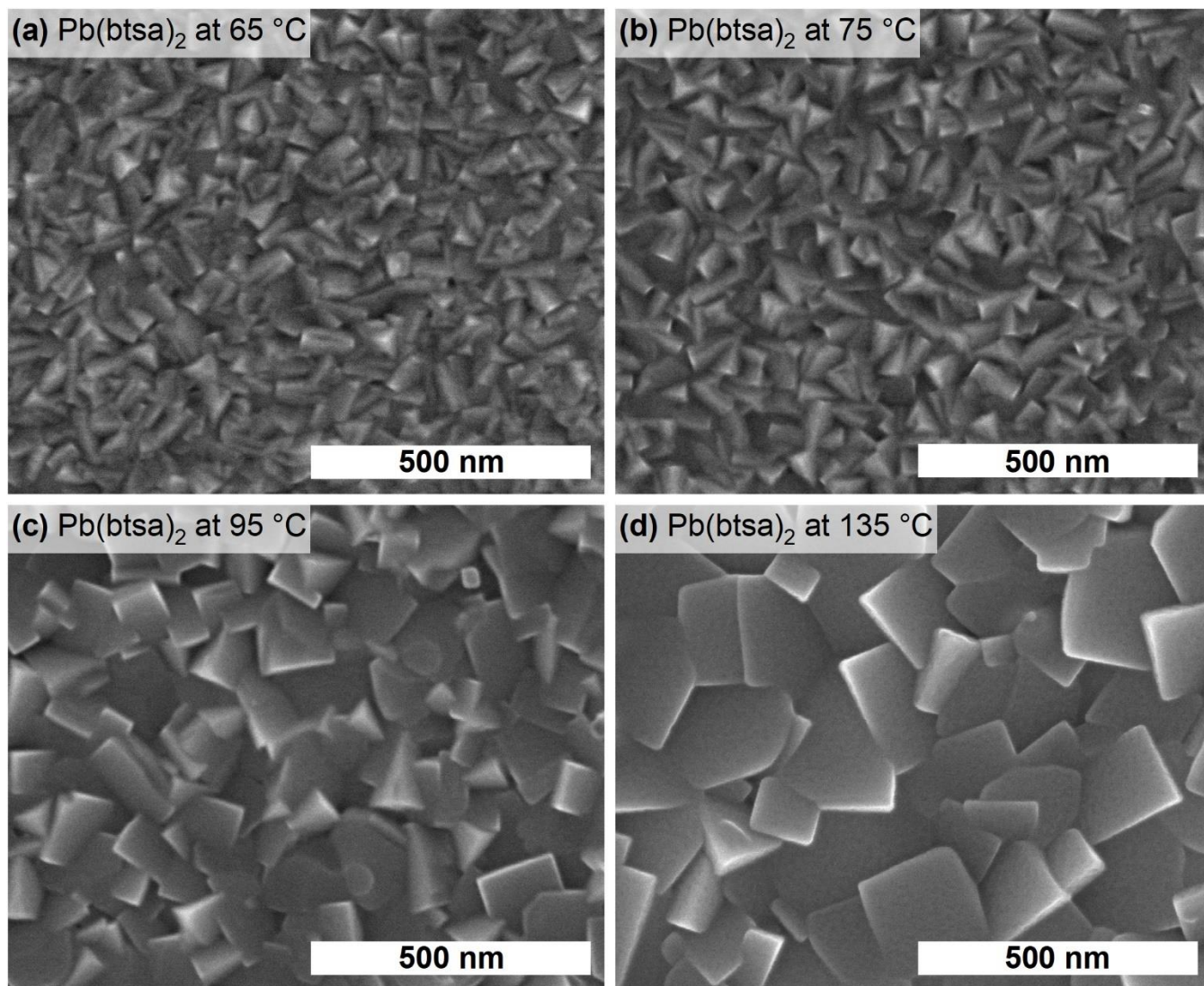


Figure S8. FESEM images of PbS films deposited at different temperatures with the $\text{Pb}(\text{btsa})_2 - \text{H}_2\text{S}$ process using 1.0 s precursor pulses and purge durations. The number of deposition cycles was chosen according to Figure 1c so that the target thickness was approximately 100 nm.

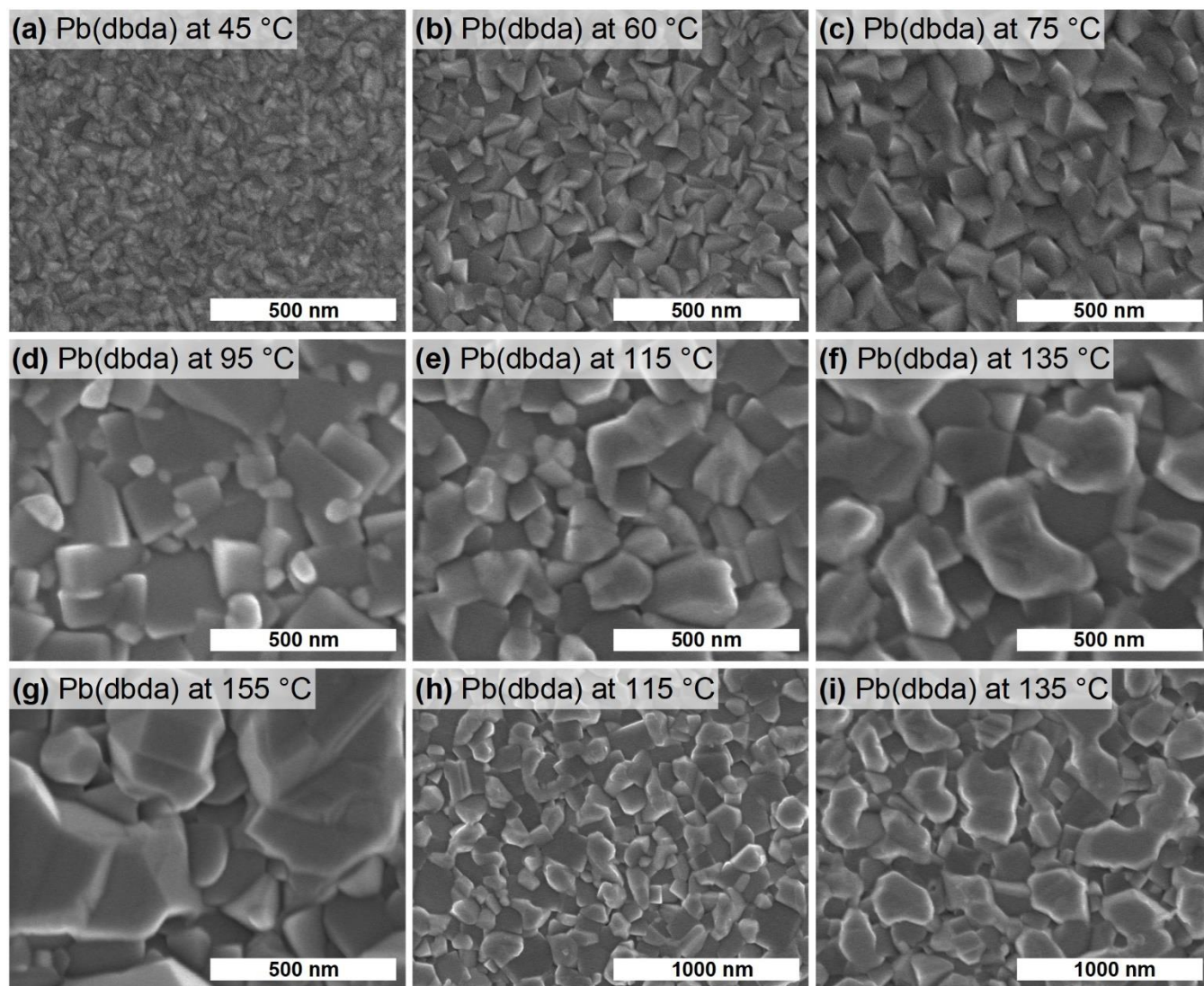


Figure S9. FESEM images of PbS films deposited at different temperatures with the Pb(dbda) – H₂S process using 1.0 s precursor pulses and purge durations. The number of deposition cycles was chosen according to Figure 1c so that the target thickness was approximately 100 nm. Note different magnifications in (h) and (i).

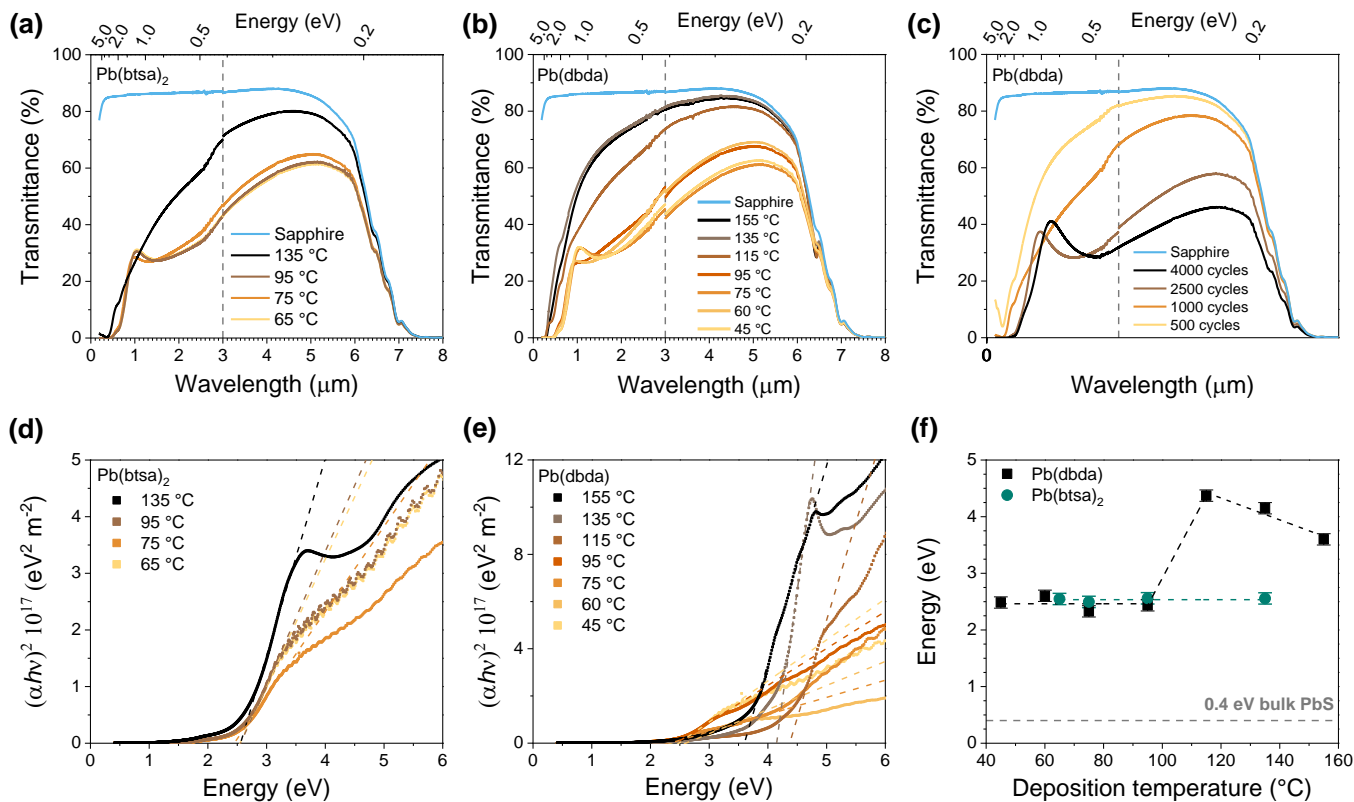


Figure S10. Transmittance of ca. 100 nm thick PbS films deposited on sapphire with (a) Pb(btsa)₂ and (b) Pb(dbda) at different temperatures. (c) Transmittance of PbS films deposited on sapphire with Pb(dbda) at 60 °C and different number of deposition cycles. (d) and (e) Tauc plots constructed from (a) and (b) respectively. (f) Optical band gaps of PbS films on sapphire as a function of deposition temperature extracted from Tauc plots in (d) and (b). Dashed grey lines in (a-c) separate wavelength ranges measured with different instruments. All films were deposited with 1.0 s precursor pulses and purge durations.

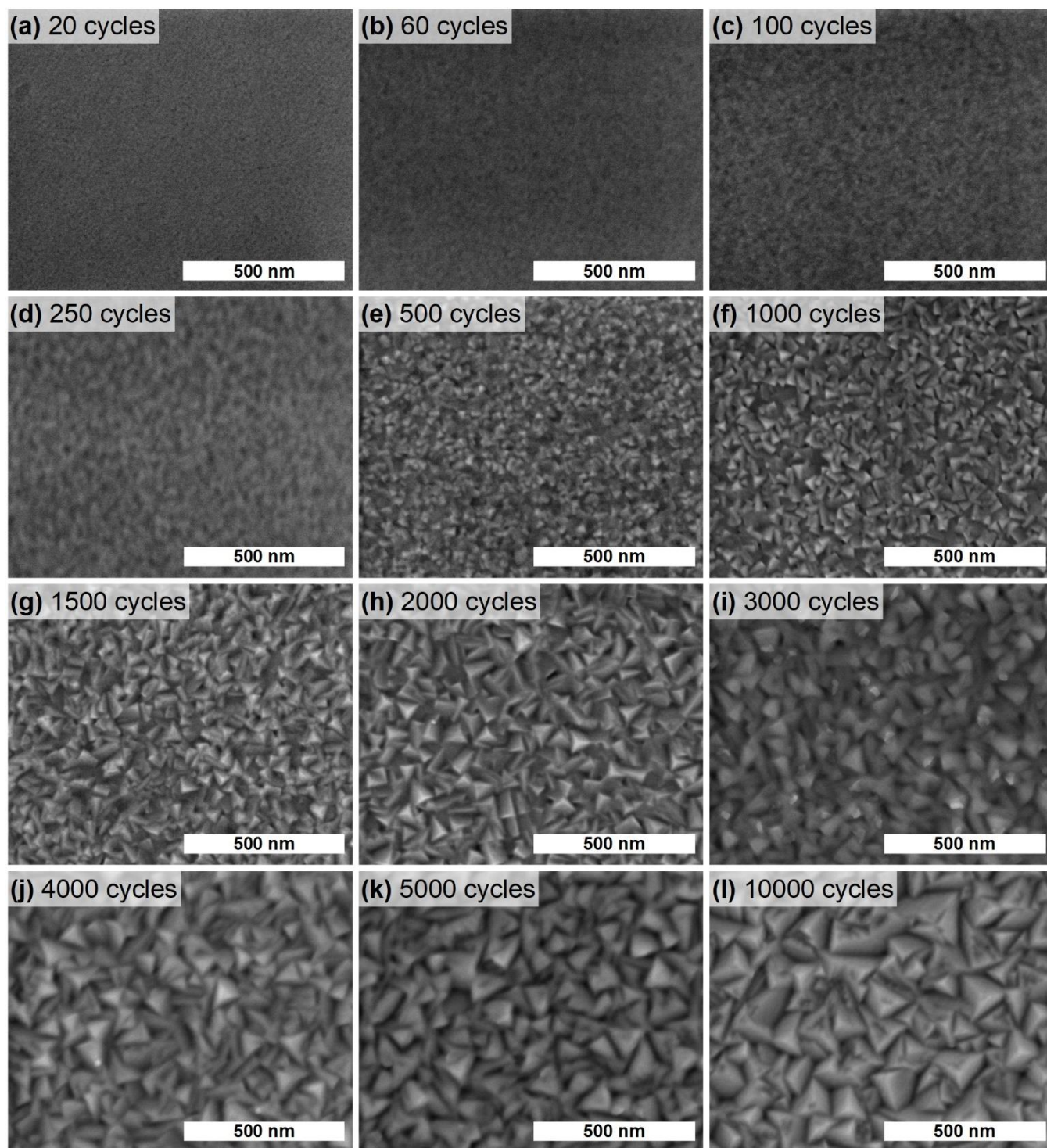


Figure S11. FESEM images of PbS films deposited with different number of cycles. The films were deposited at 75 °C with the $\text{Pb}(\text{btsa})_2 - \text{H}_2\text{S}$ process using 1.0 s precursor pulses and purge durations.

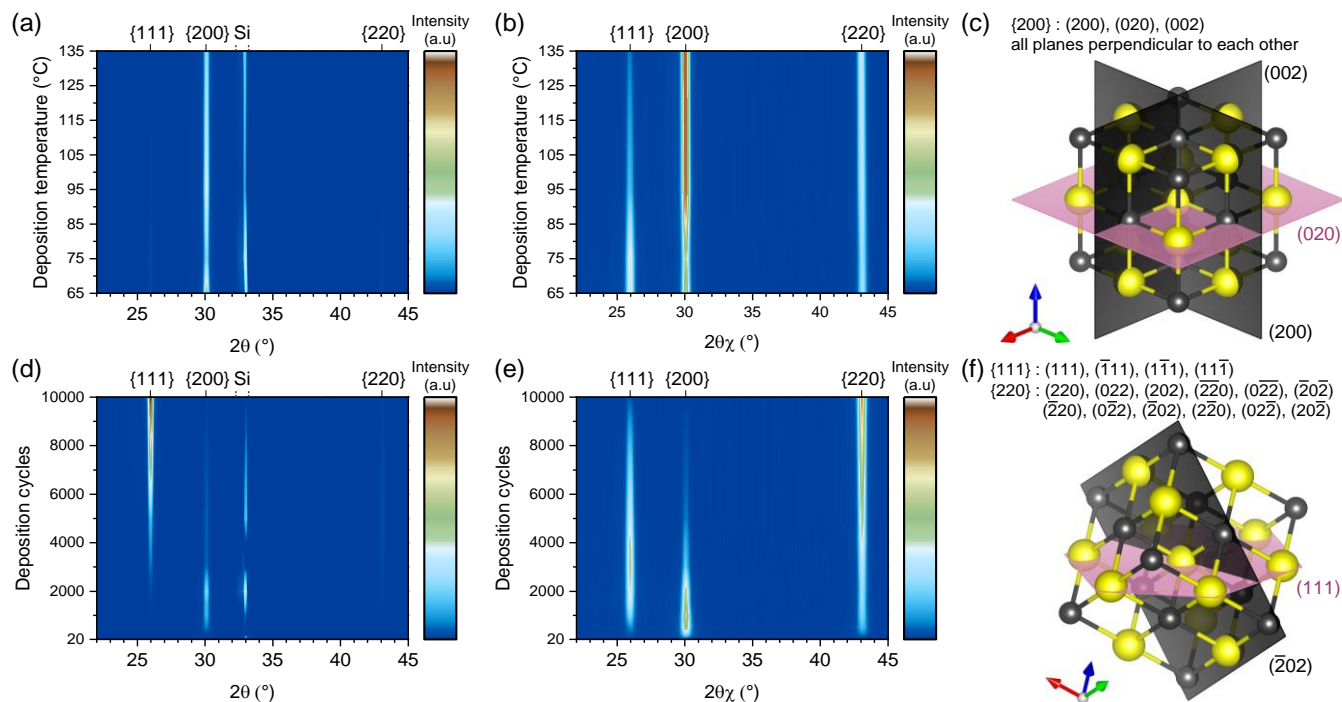


Figure S12. Contour profile maps of out of plane (a, d) and in-plane (b, e) XRD data for PbS films deposited with $\text{Pb}(\text{btsa})_2$. In (a) and (b) films are ca. 100 nm thick. In (d) and (e) films were deposited at 75 °C. All films were deposited with 1.0 s precursor pulses and purge durations. (c) and (f) show the unit cell of PbS (lead is black, sulfur is yellow), list equivalent lattice planes for a cubic unit cell that belong to the {200}, {111}, {220} families and show an example of a pair of perpendicular lattice planes that can be observed in the out of plane and in-plane measurements. Note that for {111} and {220} families only the following planes are perpendicular: $\{111\} \perp \{\bar{2}20\}, \{0\bar{2}2\}, \{\bar{2}02\}, \{2\bar{2}0\}, \{02\bar{2}\}, \{20\bar{2}\}$; $\{\bar{1}\bar{1}\bar{1}\} \perp \{220\}, \{022\}, \{\bar{2}\bar{2}0\}, \{\bar{2}0\bar{2}\}, \{0\bar{2}2\}, \{022\}$; $\{1\bar{1}\bar{1}\} \perp \{220\}, \{022\}, \{\bar{2}\bar{2}0\}, \{\bar{2}0\bar{2}\}, \{0\bar{2}2\}, \{022\}$; $\{11\bar{1}\} \perp \{220\}, \{022\}, \{\bar{2}\bar{2}0\}, \{\bar{2}0\bar{2}\}, \{0\bar{2}2\}, \{022\}$.

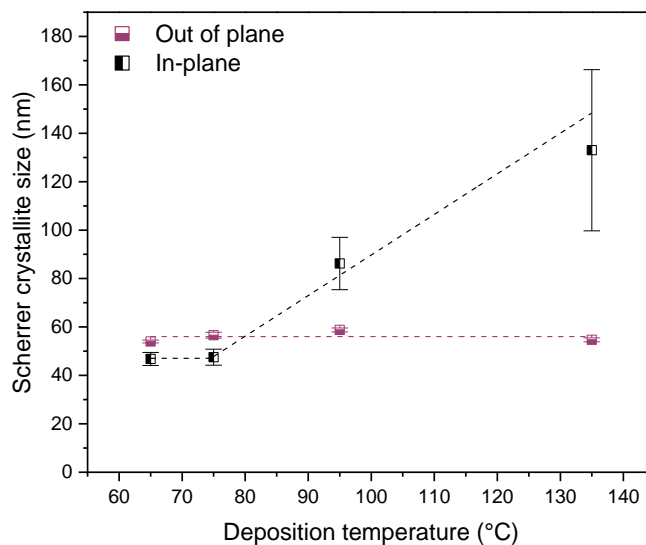


Figure S13. Out of plane and in-plane crystallite sizes in ca. 100 nm thick PbS films deposited with $\text{Pb}(\text{btsa})_2$. All films were deposited with 1.0 s pulse and purge durations.

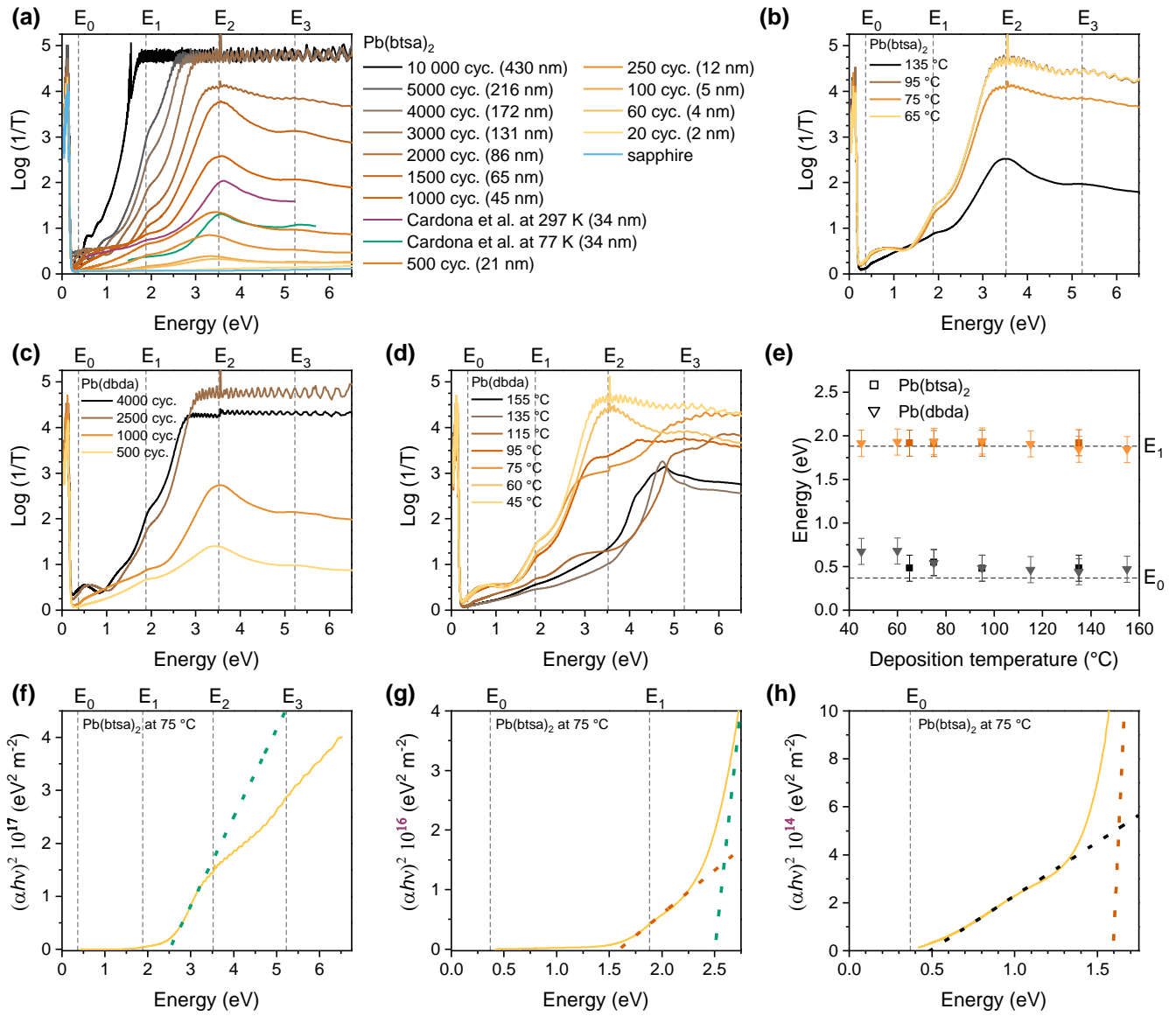


Figure S14. (a) Log (1/T) plots of PbS films deposited on sapphire with Pb(btsa)₂ at 75 °C and different number of cycles. (b) Log (1/T) plots of ca. 100 nm thick PbS films deposited on sapphire with Pb(btsa)₂ at different temperatures. (c) Log (1/T) plots of PbS films deposited on sapphire with Pb(dbda) at 60 °C and different number of cycles. (d) Log (1/T) plots of ca. 100 nm thick PbS films deposited on sapphire with Pb(dbda) at different temperatures. (e) Interband transitions energies obtained from Log (1/T) plots in (b) and (d) as a function of deposition temperature. (f-h) Tauc plot of ca. 100 nm PbS film deposited on sapphire with Pb(btsa)₂ at 75 °C. Note that changing the examined energy range and Tauc property scale ((αhν)², y-axis) allows fitting three different energies ca. 0.5 eV, 1.6 and 2.5 eV which correspond to E₀, E₁ and E₂ transitions respectively. In the analogous log (1/T) plot, see for example (b), features corresponding to these transitions are immediately visible without extensive rescaling. In all figures dashed gray lines are reference energy values by Cardona et al.¹⁷ All films were deposited with 1.0 s pulse and purge durations.

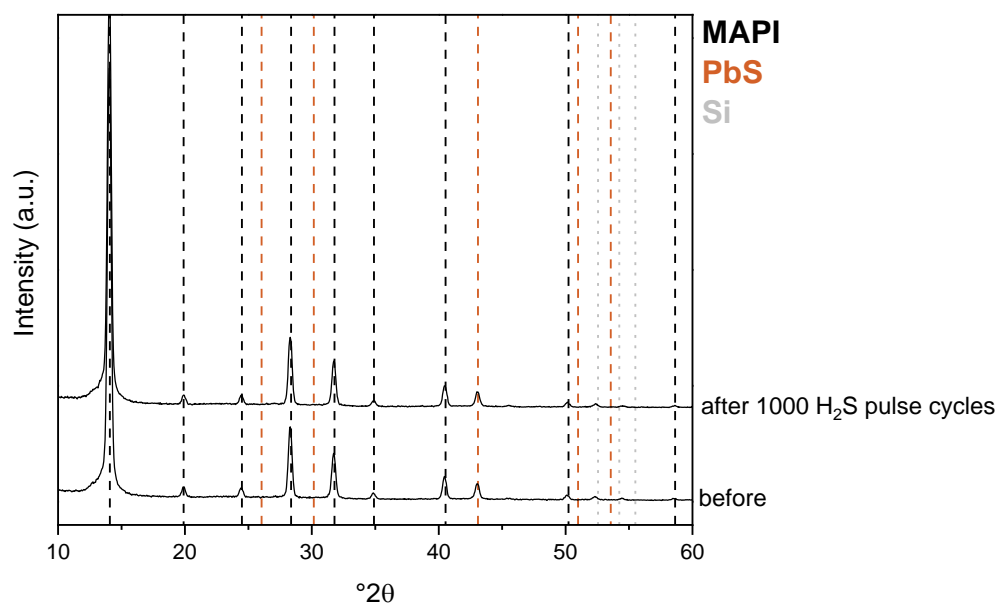


Figure S15. GIXRD pattern of a MAPI ($\text{CH}_3\text{NH}_3\text{PbI}_3$) film before and after 1000 cycles of 1.0 s long H_2S pulses separated by 3.0 s long purges at 50 °C.

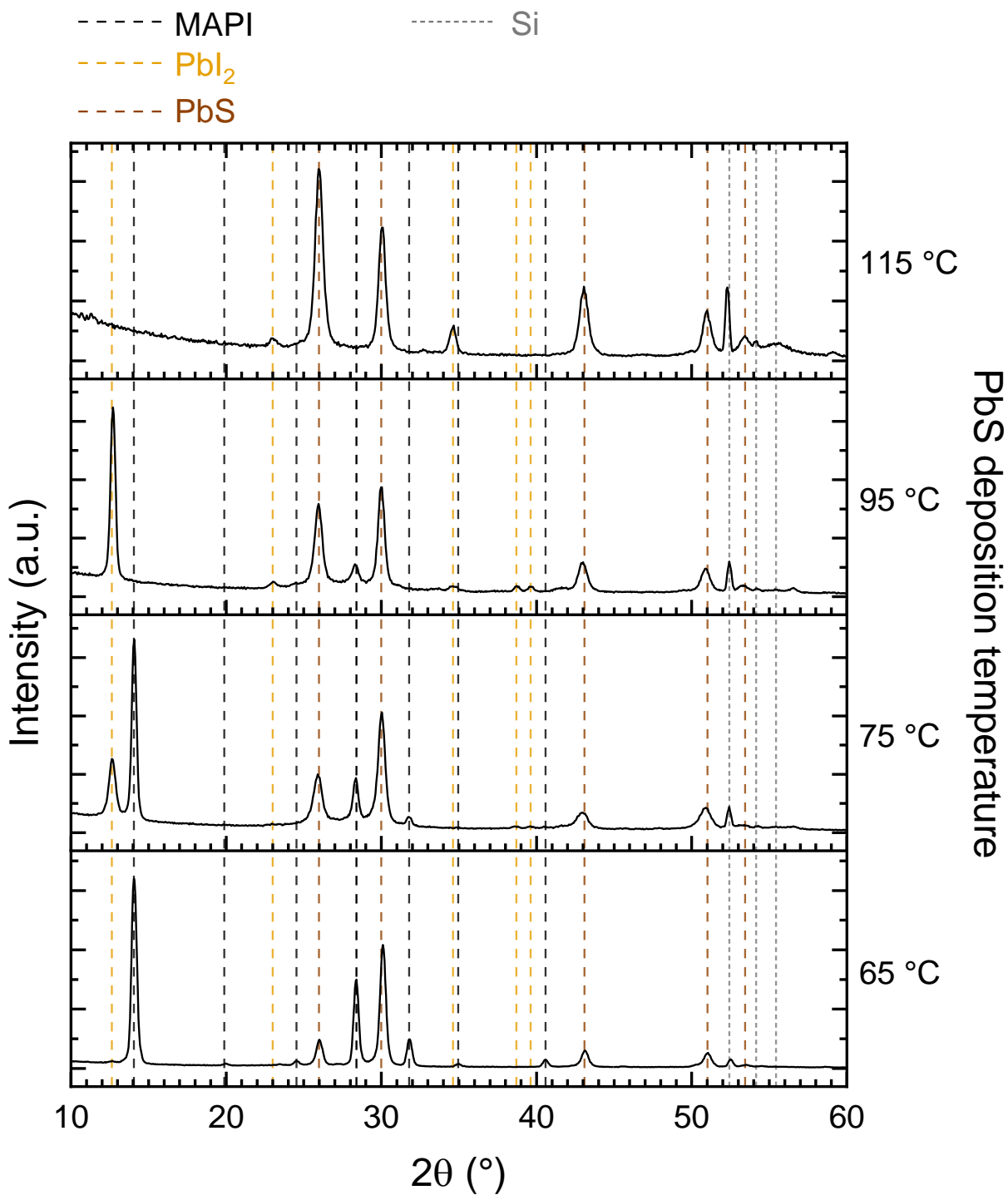


Figure S16. GIXRD patterns of samples where PbS was deposited with $\text{Pb}(\text{btsa})_2$ at different temperatures on MAPI films on silicon substrates. PbS was deposited with 1000 cycles, 1.0 s precursor pulses and purge durations.

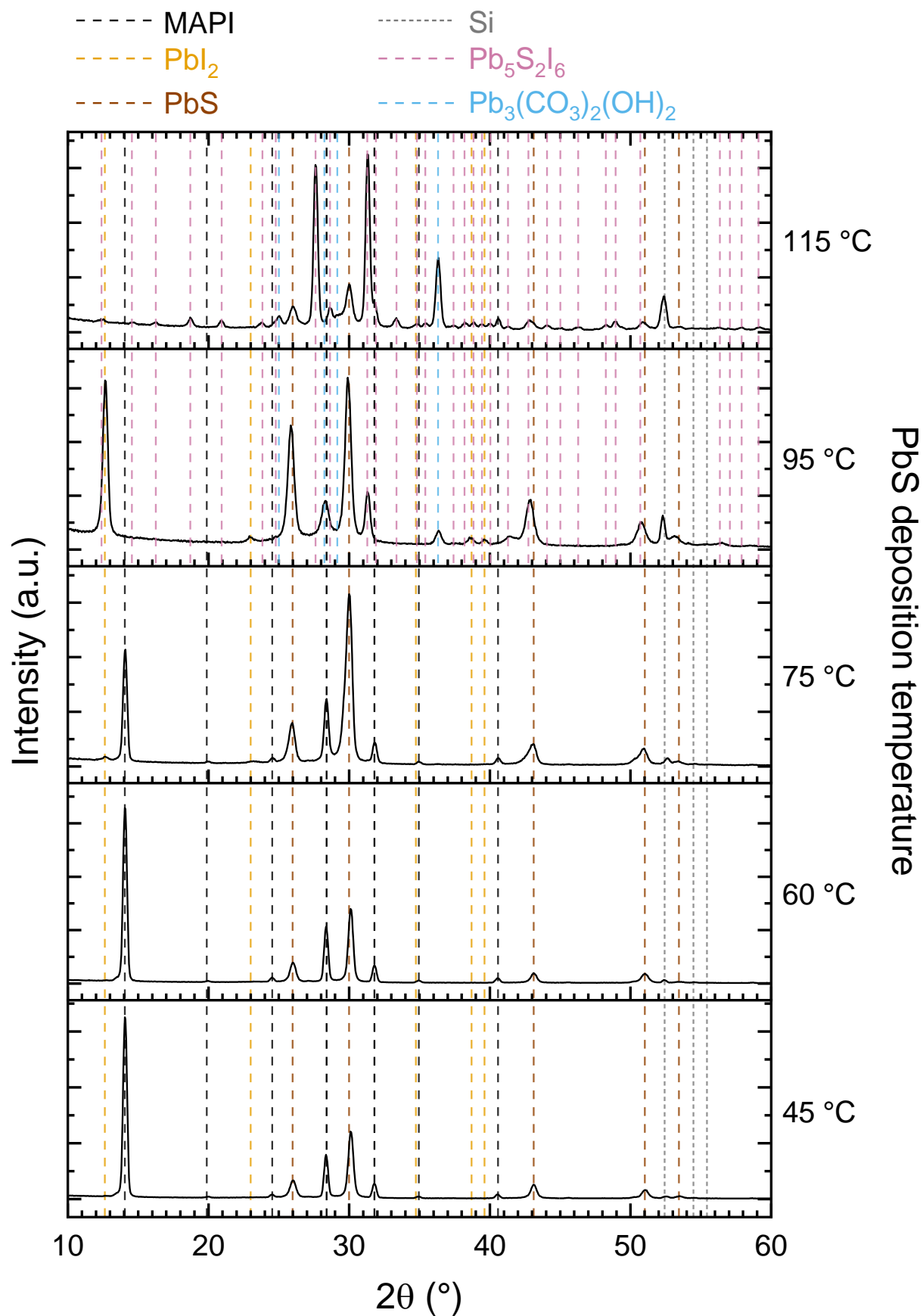


Figure S17. GIXRD patterns of samples where PbS was deposited with Pb(dbda) at different temperatures on MAPI ($\text{CH}_3\text{NH}_3\text{PbI}_3$) films on silicon substrates. PbS was deposited with 1000 cycles, 1.0 s precursor pulses and purge durations.

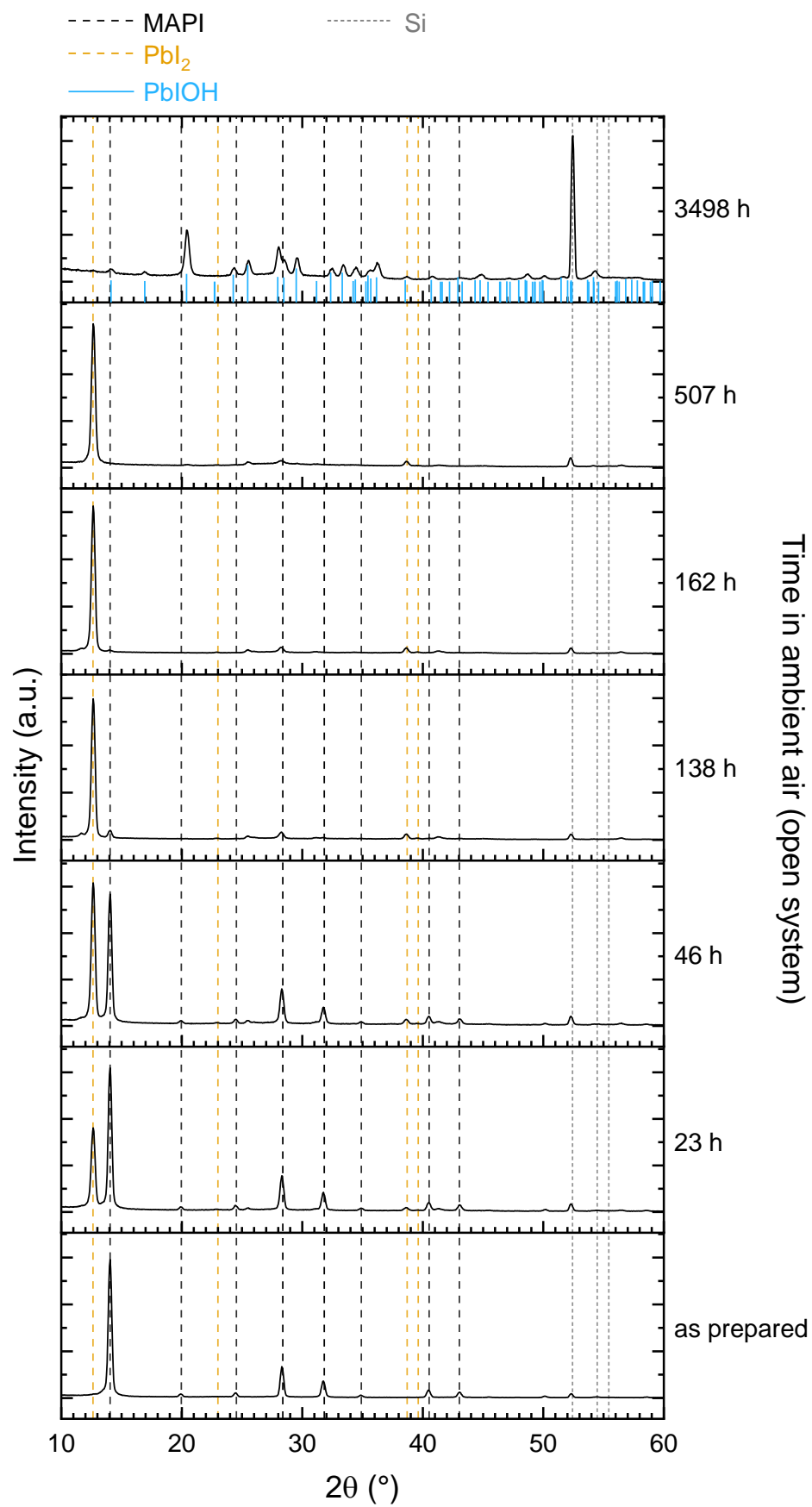


Figure S18. GIXRD patterns of MAPI film stored in ambient air.

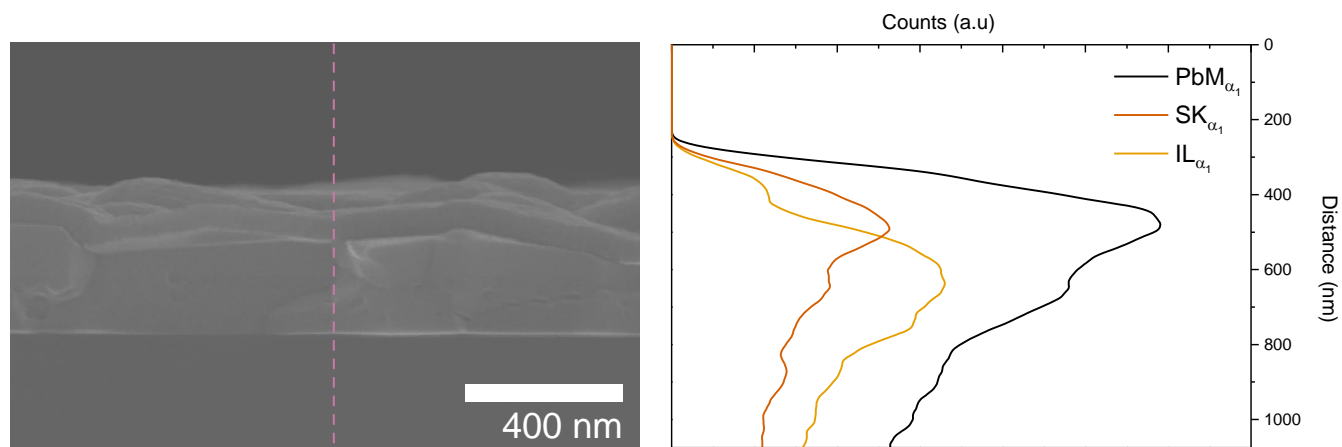


Figure S19. Cross-section SEM image of a PbS capped MAPI and EDS line scans along the purple line. PbS was deposited with Pb(dbda) at 45 °C with 1000 cycles of 1.0 s long pulse and purge durations. To examine the cross section the sample was broken in half after being stored in air for 413 days. The EDS line scan data was smoothed (adjacent averaging) for clarity. Note also the partial overlap between PbM $_{\alpha_1}$ and SK $_{\alpha_1}$ lines.

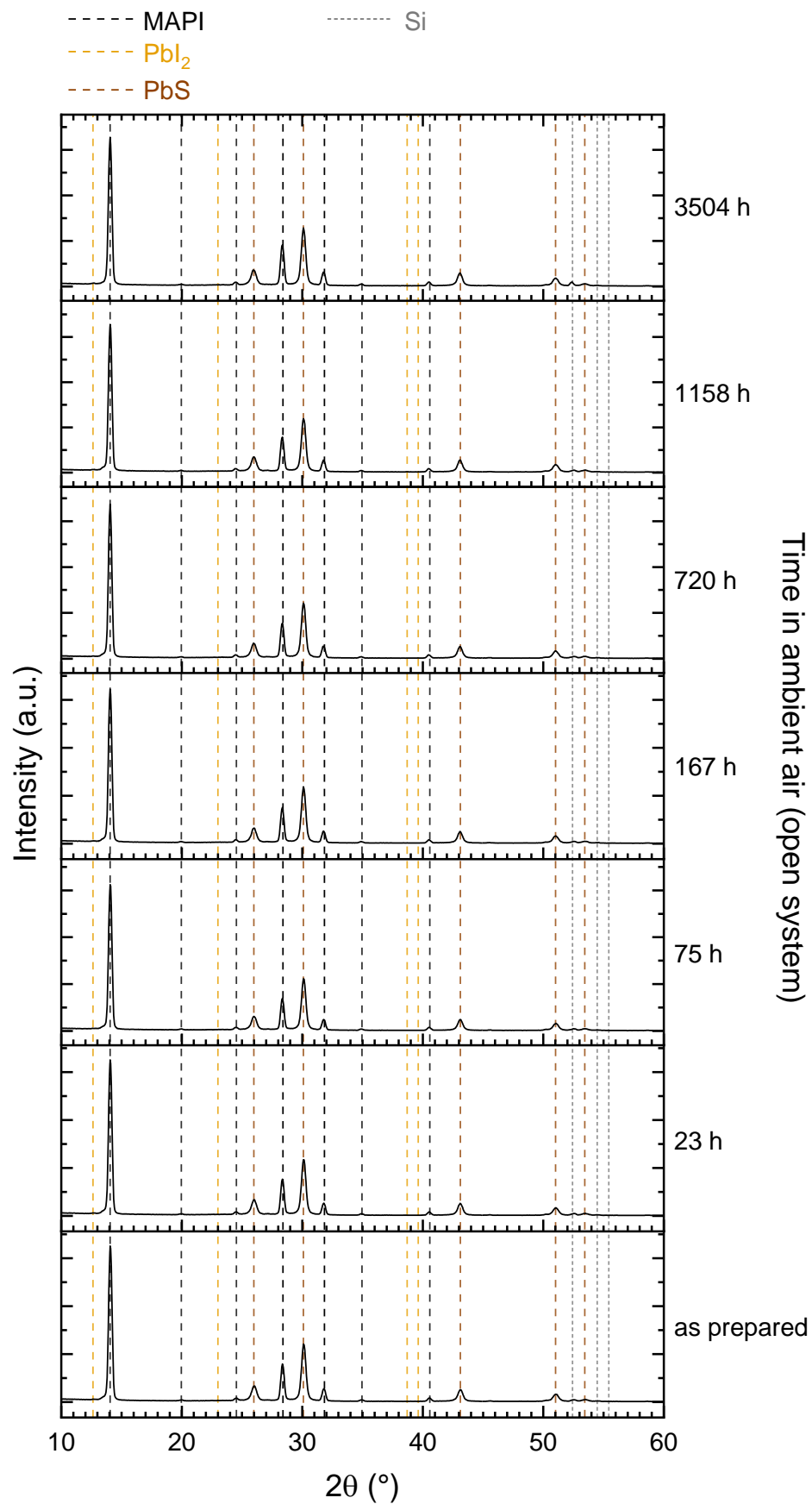


Figure S20. GIXRD patterns of a MAPI film capped with a PbS film and stored in ambient air. PbS was deposited with Pb(dbda) at 45 °C with 1000 cycles and 1.0 s precursor pulses and purge durations. The capping film thickness estimated from GPC on Si is 66 nm.

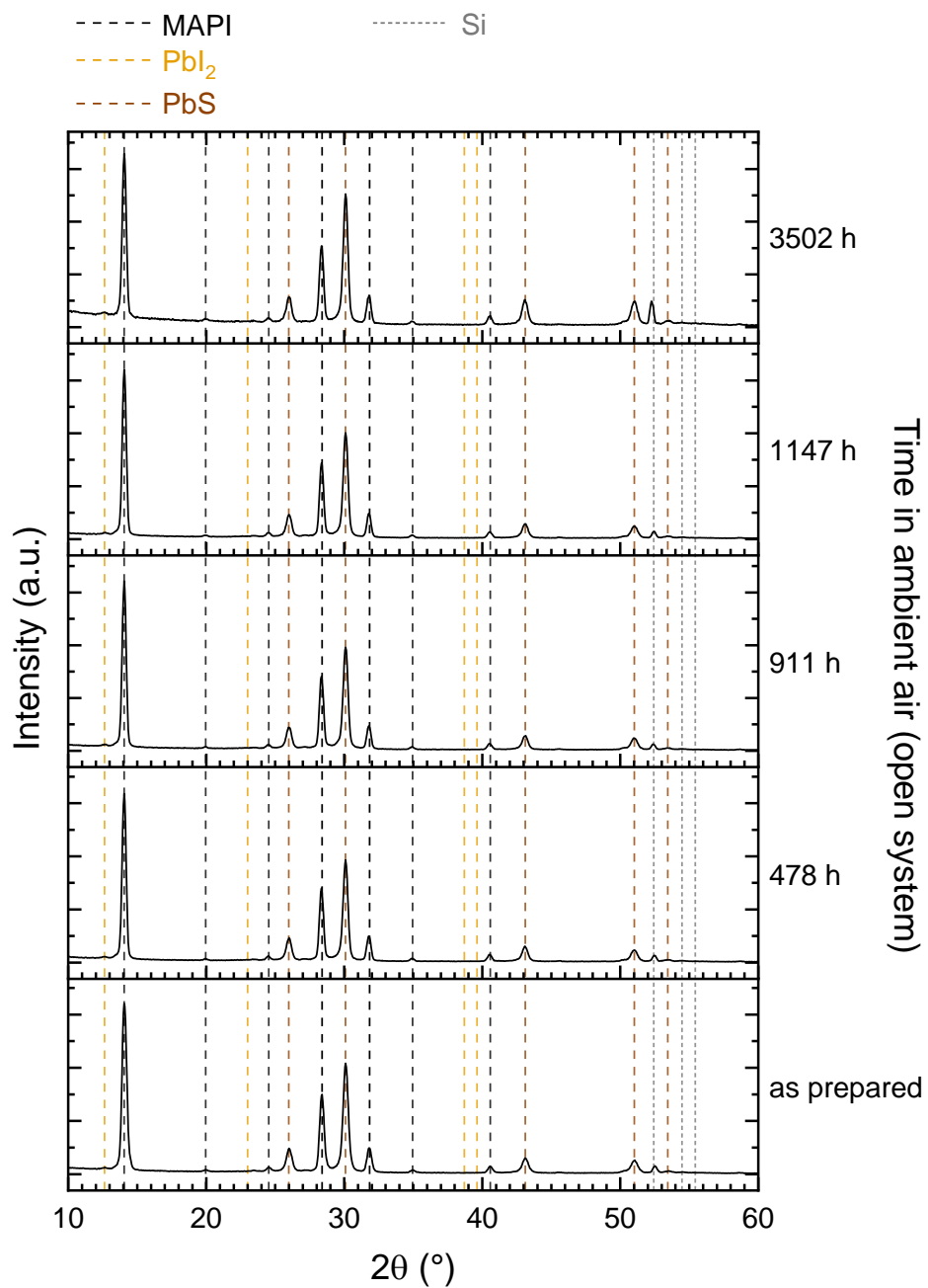


Figure S21. GIXRD patterns of a MAPI film capped with a PbS film and stored in ambient air. PbS was deposited with $\text{Pb}(\text{btsa})_2$ at 65 °C with 1000 cycles and 1.0 s precursor pulses and purge durations. The capping film thickness estimated from GPC on Si is 50 nm.

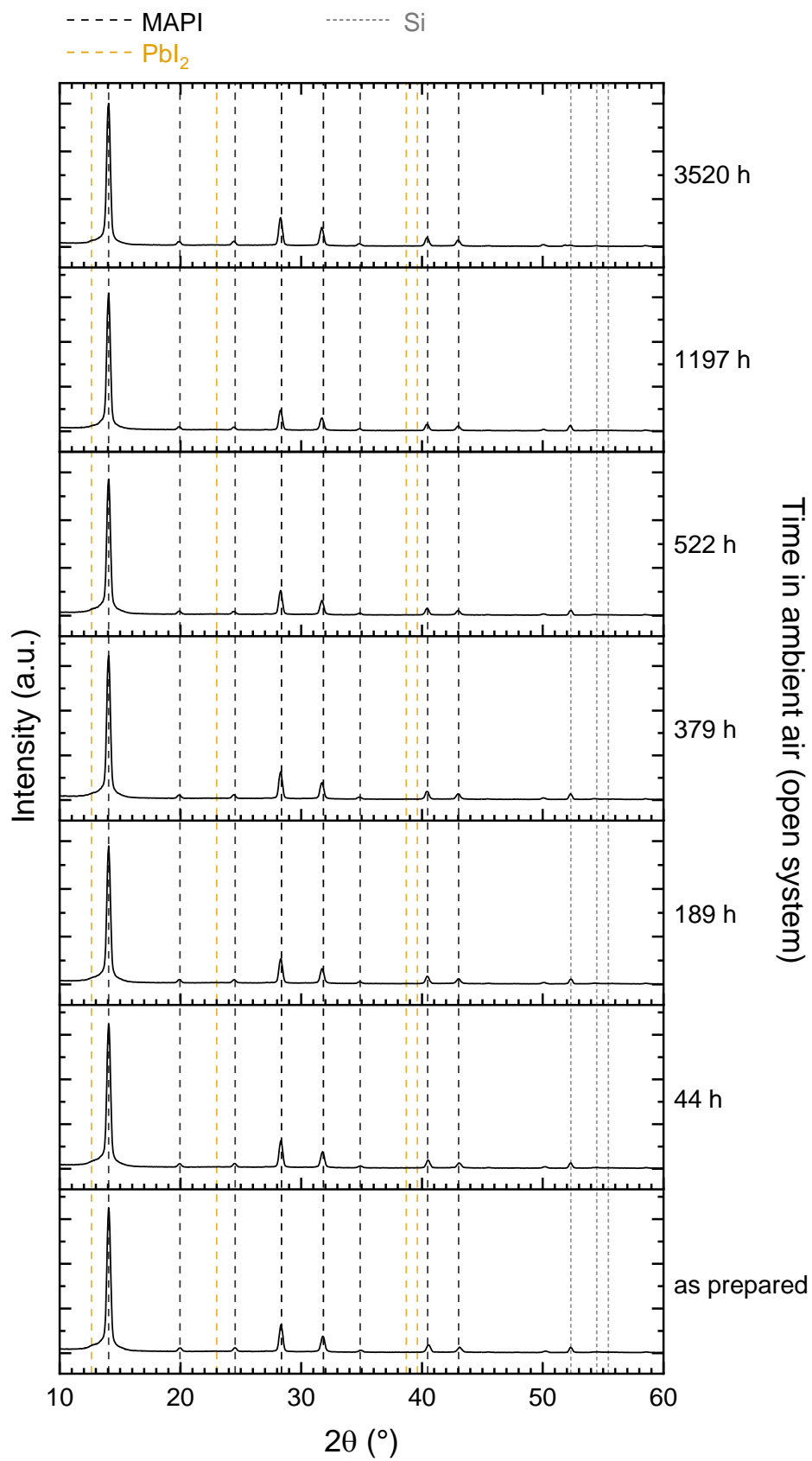


Figure S22. GIXRD patterns of a MAPI film capped with an Al_2O_3 film and stored in ambient air. Al_2O_3 was deposited with the TMA - H_2O process at 65°C with 800 cycles, 1.0 s precursor pulses and 4.0 s purge durations. The capping film thickness estimated from GPC on Si is 52 nm.

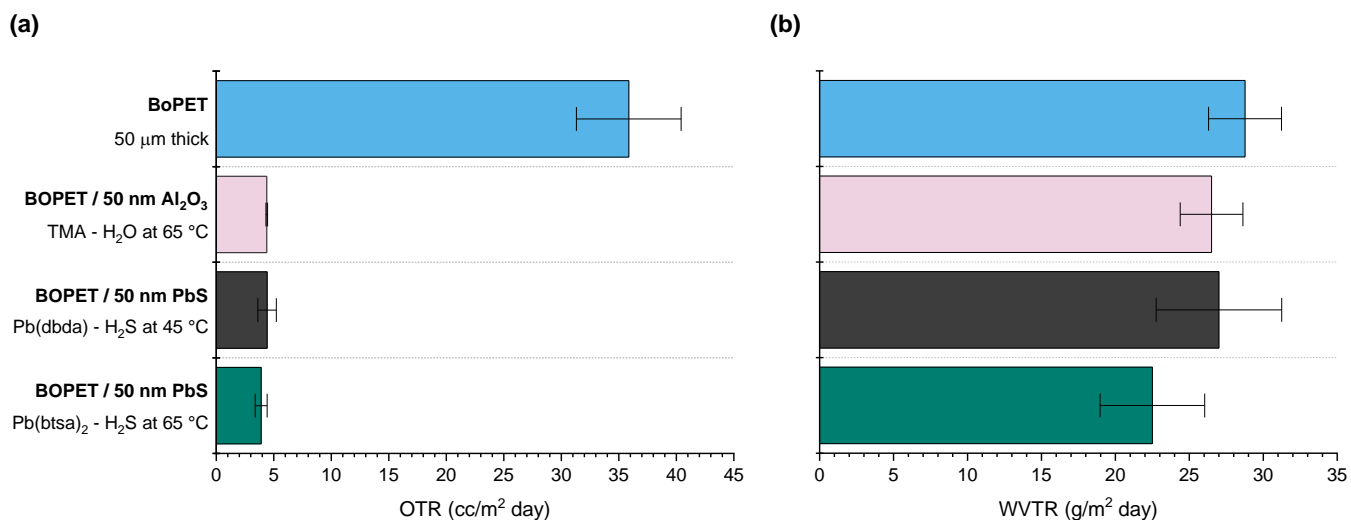


Figure S23. (a) Oxygen transmission rates and (b) water vapor transmission rates for bare BoPET and BoPET with an ALD film deposited on it. Al₂O₃ films were deposited with 1.0 s precursor pulses and 4.0 s purge durations. PbS films were deposited with 6.0 s precursor pulses and 3.0 s purge durations.

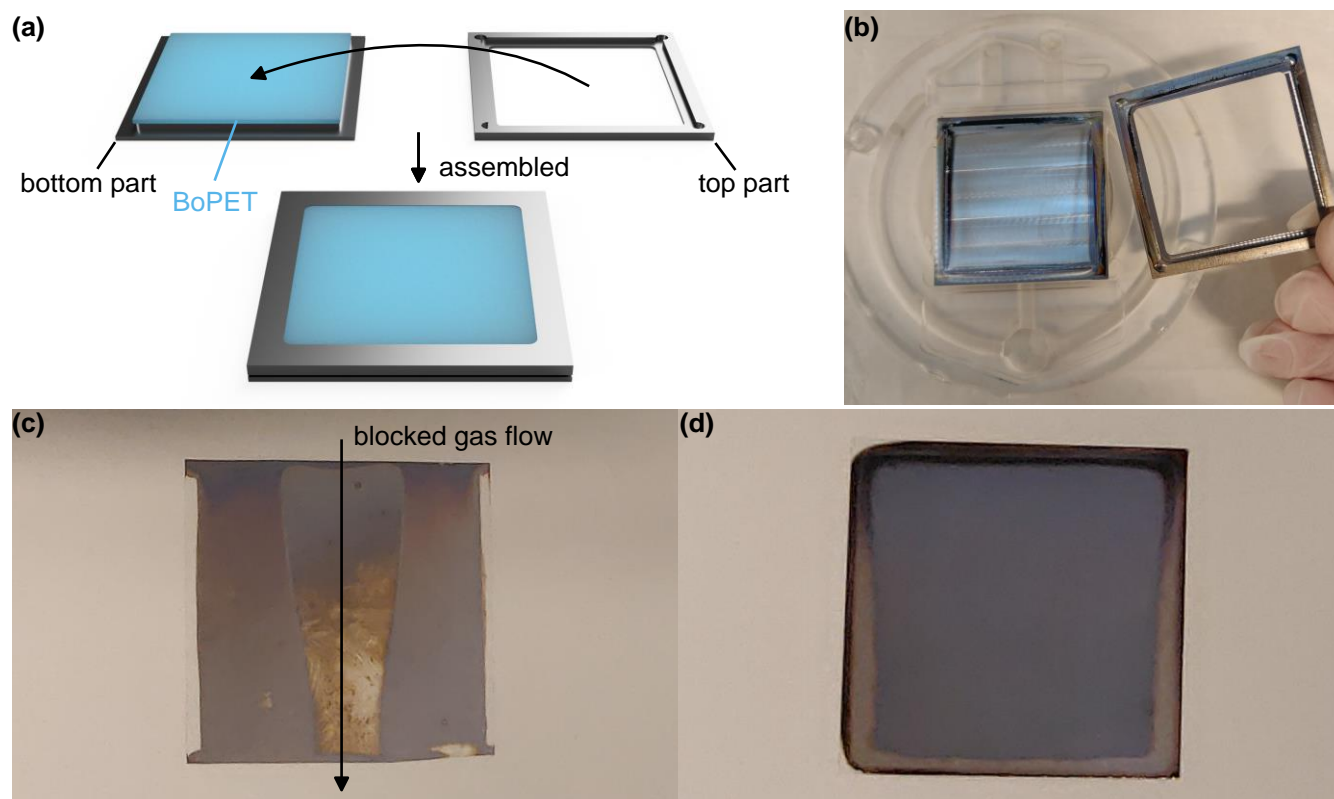


Figure S24. (a) 3D model and (b) photograph of an adapter machined from Al for depositions on BoPET. (c) BoPET after PbS deposition without using the adapter. The polymer had moved and bent inside the substrate cassette, causing a partial blockage of the gas flow. (b) BoPET after PbS deposition with the adapter.

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